

AMENDMENTS TO THE CLAIMS

The following listing of claims will replace all prior versions and listings of claims in the application.

LISTING OF CLAIMS

Not Entered
llg
~~1-13. (cancelled).~~

14. (withdrawn) A photoelectrode comprising a semiconductor layer having first and second opposite major surfaces, said first major surface overlaid with a layer of indium tin oxide (ITO) having a thickness of at least 4000 Angstroms.

15. (withdrawn) The photoelectrode of claim 14 wherein said semiconductor layer comprises photovoltaic, amorphous, silicon n-i-p material; and said indium tin oxide layer overlies p of said n-i-p.

16. (withdrawn) The photoelectrode of claim 14 wherein said semiconductor layer second major surface is in contact with an electrically conductive substrate.

17. (withdrawn) The photoelectrode of claim 16 wherein said photoelectrode comprises in order: said electrically conductive substrate comprising ss/Ag/ZnO, and said semiconductor comprising n-i-p; wherein said n-layer faces said ZnO, and said ITO layer overlies said p-layer.